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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE **Application Number** 09/945,535 STATEMENT BY APPLICANT Filing Date August 30, 2001 Ahn, Kie **First Named Inventor** EEB 0 8 JUUR **Group Art Unit** 2813 Rodgers, Colleen **Examiner Name** Attorney Docket No: 1303.026US1 Sheet 1 of 4

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	Group Art Unit	2813	
Sheet 2 of 4	Examiner Name	Rodgers, Colleen	
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